

THE SPECIFICATION OF AlGaAs PR LED CHIP “YL-C670nm-0.07mW”

1. DESCRIPTION

This is a AlGaAs red LED chip. It is N-side up. The peak wavelength is 670 nm (Typ.).

2. ELECTRO - OPTICAL CHARACTERISTICS (Ta=25°C)

CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage (V _F) IF=7.2mA		1.70		V
Reverse Voltage (V _R) IR=10 μ A	4			V
or Reverse Current (I _R) Vr=4V			10	(μ A)
Radiated Power ¹⁾ (Po) IF=6.3mA	0.07			mW
Peak Wavelength (λ _p) IF=5mA	655	670	685	nm
Spectral Radiation Bandwidth (Δλ) IF=5mA		23		nm
Rise Time (Tr) IFp=6.3mA Tw=125ns,Duty=50%		30		ns
Fall Time (Tf) IFp=6.3mA Tw=125ns,Duty=50%		30		ns

1) LED chip is mounted on TO-18 gold header without resin coated.

3. ABSOLUTE MAXIMUM RATINGS

Continuous Maximum Forward Current	: 20 mA(DC)
Reverse Voltage	: 4 V(IR=10 μ A)
Storage Temperature	
while on mylar membrane	: 0 to 40 °C
after removal from mylar membrane	: -40 to 100 °C

4. PHYSICAL CHARACTERISTICS AND STRUCTURE

- 1) Material : AlGaAs
- 2) Structure : Hetero Structure
- 3) Junction Size : 0.280mm × 0.280mm
- 4) Thickness : 0.280mm
- 5) Bond Pad Size : 0.140mm diameter
- 6) Anode Metallization : Gold Alloy
- 7) Cathode Metallization: Gold Alloy

5.Physical Dimensions

Model YL-C670nM-0.07mW

